

## SPECIFICATION OF LED CHIP

C1200-35

[NIR]

### 1) Commodity Type and Physical Characteristics.

- |                      |   |
|----------------------|---|
| 1. Material          | InGaAsP/InP(DDH)  |
| 2. Electrode         | Top Side P (anode) side : Au Alloy<br>Bottom Side N (cathode) side : Au Alloy |
| 3. Electrode Pattern | Fig.1   |
| 4. Chip Size         | Fig.2   |
| 5. Chip Thickness    | Fig.2   |
| 6. Emission Area     | Fig.2   |

### 2) Electro-Optical Characteristics

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	V <sub>f</sub>	I <sub>f</sub> =20mA		0.8	1.3	V
Reverse Current	I <sub>r</sub>	V <sub>r</sub> =3V			10	uA
Power Intensity	P <sub>o</sub>	I <sub>f</sub> =20mA		0.6		mW
Peak Wavelength	λ <sub>P</sub>	I <sub>f</sub> =20mA	1150	1200	1250	nm
Spectral Radiation Bandwidth	Δλ	I <sub>f</sub> =20mA		100		nm
RiseTime	t <sub>r</sub>	I <sub>f</sub> =20mA		10		ns
FallTime	t <sub>f</sub>	I <sub>f</sub> =20mA		10		ns

‡ Die shall be mounted on TO=18 gold header without resin coated. (T<sub>a</sub>=25°C)

[Unit: um]

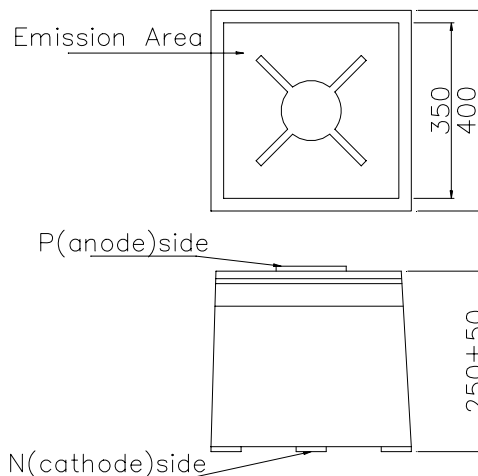
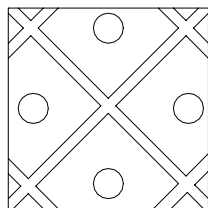
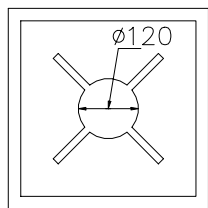


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area